

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	748	abe near hiroyuki.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
2	BRS	L2	5	1 and (electro-optic near device)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
3	BRS	L3	6494	(silicon near nitride) near25 (aperture\$1 or hole\$1)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
4	BRS	L4	2	((silicon near nitride) near25 (aperture\$1 or hole\$1)) near25 (display near element\$)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
5	BRS	L5	1	((silicon near nitride) near25 (aperture\$1 or hole\$1)) near25 (el near element\$)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
6	BRS	L6	4	((silicon near nitride) near25 (aperture\$1 or hole\$1)) near25 (el)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
7	BRS	L7	1736	((silicon near nitride) near25 (aperture\$1 or hole\$1)) near25 (electro\$8)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
8	BRS	L8	16	((silicon near nitride) near25 (display) near25 (aperture\$1 or hole\$1)) near25 (electro\$8))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
9	BRS	L9	9	((silicon near nitride) near25 (display) near25 (open\$3)) near25 (electro\$8))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
10	BRS	L10	2	((silicon near nitride) near25 (display) near25 (open\$3)) near25 (element\$1))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
11	BRS	L11	5	((silicon near nitride) near25 (display) near25 (aperture\$1 or hole\$1 or via\$1)) near25 (element\$1))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
12	BRS	L12	434	((silicon near nitride) near25 (aperture\$1 or hole\$1 or via\$1)) near25 (element\$1))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
13	BRS	L13	146	(((((silicon near nitride) near25 (aperture\$1 or hole\$1 or via\$1)) near25 (element\$1))) near25 (substrate)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
14	BRS	L14	66	13 and "257"/\$.ccls.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
15	BRS	L15	1	(((((silicon near nitride) near25 (aperture\$1 or hole\$1 or via\$1)) near25 (element\$1))) near25 (pixel near electrode) near25 (substrate)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
16	BRS	L16	2	(((((silicon near nitride) near25 (aperture\$1 or hole\$1 or via\$1)) near25 (element\$1))) near25 (pixel) near25 (substrate)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
17	BRS	L17	504	(pixel near electrode\$1) near25 (silicon near nitride)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
18	BRS	L18	446	(pixel near electrode\$1) near15 (silicon near nitride)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
19	BRS	L19	58	((pixel near electrode\$1) near15 (silicon near nitride)) near25 (hole\$1 or aperture\$1 or via\$1 or recess\$2)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	U	1	Document ID	Title
1			US 20040246424 A1	Substrate for liquid crystal display and liquid crystal display utilizing the same
2			US 20040224456 A1	Electro-optic device, method to manufacture the same and electronic apparatus
3			US 6452580 B1	Active matrix liquid crystal display device
4			JP 2004296303 A	Organic electroluminescent display device for mobile telephone, has silicon nitride film with holes formed corresponding to organic electroluminescent elements formed on transparent substrate
5			JP 11111990 A	Thin film transistor for use as switching element for pixel display in active matrix display device - includes silicon oxide films on substrate, between which silicon nitride film is pinched where source-drain electrodes are formed in through holes formed in silicon nitride film